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Team Nexperia



PBRP113ZT

PNP 800 mA, 40 V BISS RET; R1 = 1 k Ω , R2 = 10 k Ω

Rev. 01 — 16 January 2008

Product data sheet

1. Product profile

1.1 General description

800 mA PNP low V_{CEsat} Breakthrough In Small Signal (BISS) Resistor-Equipped Transistor (RET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBRN113ZT.

1.2 Features

- 800 mA repetitive peak output current
- High current gain h_{FF}
- Built-in bias resistors
- Simplifies circuit design
- Low collector-emitter saturation voltage
 V_{CFsat}
- Reduces component count
- Reduces pick and place costs
- ±10 % resistor ratio tolerance

1.3 Applications

- Digital application in automotive and industrial segments
- Medium current peripheral driver
- Switching loads

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	-40	V
Io	output current		[1][2]	-	-	-600	mA
I _{ORM}	repetitive peak output current	$t_p \leq 1 \text{ ms}; \\ \delta \leq 0.33$	[3]	-	-	-800	mA
R1	bias resistor 1 (input)			0.7	1	1.3	kΩ
R2/R1	bias resistor ratio			9	10	11	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for collector 1 cm².



^[2] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

PNP 800 mA, 40 V BISS RET; R1 = 1 k Ω , R2 = 10 k Ω

2. Pinning information

Table 2. Pinning

Table 2.	Filling		
Pin	Description	Simplified outline	Symbol
1	input (base)		
2	GND (emitter)	3	3
3	output (collector)	1 2	1 R2 2 sym003

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBRP113ZT	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PBRP113ZT	*7M

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

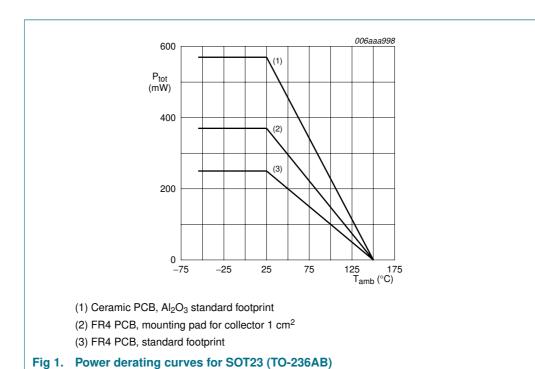
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-40	V
V_{CEO}	collector-emitter voltage open base		-	-40	V
V_{EBO}	emitter-base voltage open collector		-	- 5	V
V_{I}	input voltage				
	positive		-	+5	V
	negative		-	-10	V
Io	output current		[1][2]	-600	mA
I _{ORM}	repetitive peak output current	$t_p \le 1 \text{ ms};$ $\delta \le 0.33$	[3] -	-800	mA

PNP 800 mA, 40 V BISS RET; R1 = 1 k Ω , R2 = 10 k Ω

Table 5. Limiting values ...continued In accordance with the Absolute Maximum Rating System (IEC 60134).

		0 , (,		
Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot} tota	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
			[3] _	250	mW
			<u>[1]</u> -	370	mW
			[2] _	570	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [2] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



PBRP113ZT_1

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PNP 800 mA, 40 V BISS RET; R1 = 1 k Ω , R2 = 10 k Ω

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
() \(\omega\)	thermal resistance from	in free air				
	junction to ambient		[1]	-	500	K/W
			[2]	-	338	K/W
			[3]	-	219	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	105	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

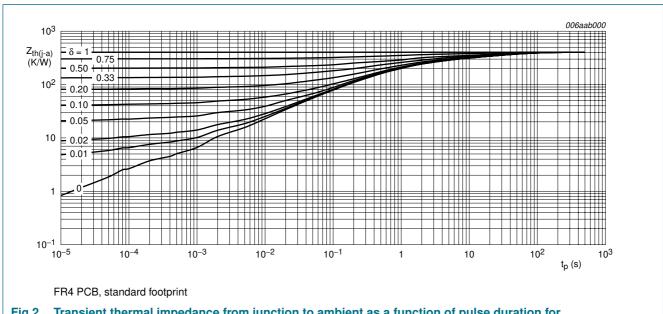
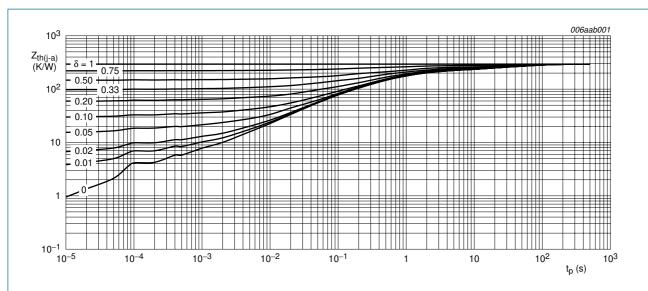


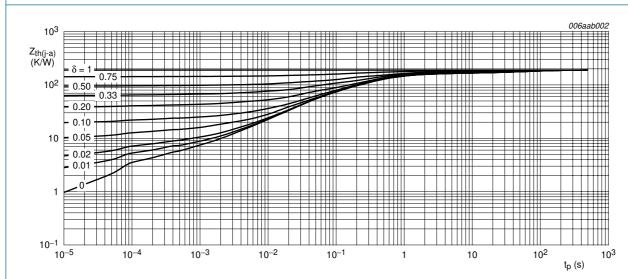
Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23 (TO-236AB); typical values

PNP 800 mA, 40 V BISS RET; R1 = 1 k Ω , R2 = 10 k Ω



FR4 PCB, mounting pad for collector 1 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23 (TO-236AB); typical values



Ceramic PCB, Al₂O₃ standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23 (TO-236AB); typical values

PNP 800 mA, 40 V BISS RET; R1 = 1 k Ω , R2 = 10 k Ω

7. Characteristics

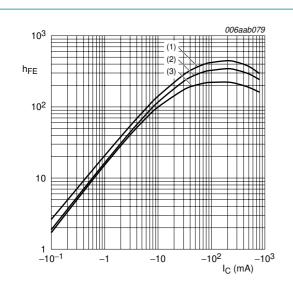
Table 7. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V};$ $I_E = 0 \text{ A}$		-	-	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V};$ $I_{B} = 0 \text{ A}$		-	-	-0.5	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V};$ $I_C = 0 \text{ A}$		-	-	-0.8	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -50 \text{ mA}$		190	270	-	
		$V_{CE} = -5 \text{ V};$ $I_{C} = -300 \text{ mA}$	<u>[1]</u>	230	320	-	
		$V_{CE} = -5 \text{ V};$ $I_{C} = -600 \text{ mA}$	[1]	190	270	-	
0 = 0 0 1	collector-emitter saturation voltage	$I_C = -50 \text{ mA};$ $I_B = -2.5 \text{ mA}$		-	- 35	-4 5	mV
		$I_C = -200 \text{ mA};$ $I_B = -10 \text{ mA}$		-	- 70	-100	mV
		$I_C = -500 \text{ mA};$ $I_B = -10 \text{ mA}$	<u>[1]</u>	-	-200	-300	mV
		$I_C = -600 \text{ mA};$ $I_B = -6 \text{ mA}$	<u>[1]</u>	-	-45 0	-75 0	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V};$ $I_{C} = -100 \mu\text{A}$		-0.3	-0.5	-1	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V};$ $I_{C} = -20 \text{ mA}$		-0.4	-0.7	-1.4	V
R1	bias resistor 1 (input)			0.7	1	1.3	kΩ
R2/R1	bias resistor ratio			9	10	11	
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	11	-	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

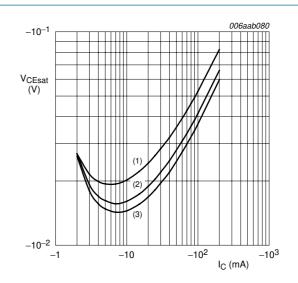
PNP 800 mA, 40 V BISS RET; R1 = 1 k Ω , R2 = 10 k Ω



$$V_{CE} = -5 \text{ V}$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

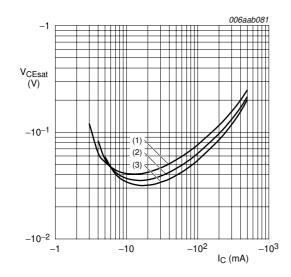
Fig 5. DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

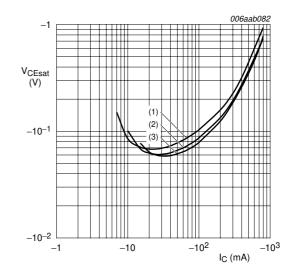
Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values





- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values

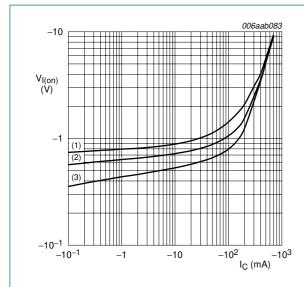


$$I_{\rm C}/I_{\rm B} = 100$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values

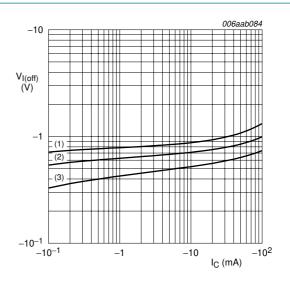
PNP 800 mA, 40 V BISS RET; R1 = 1 k Ω , R2 = 10 k Ω



$$V_{CE} = -0.3 \text{ V}$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 9. On-state input voltage as a function of collector current; typical values

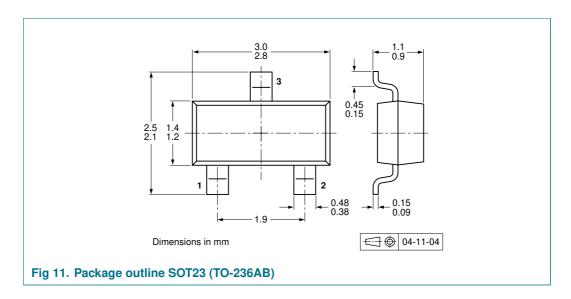


$$V_{CE} = -5 \text{ V}$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 10. Off-state input voltage as a function of collector current; typical values

8. Package outline



PNP 800 mA, 40 V BISS RET; R1 = 1 k Ω , R2 = 10 k Ω

9. Packing information

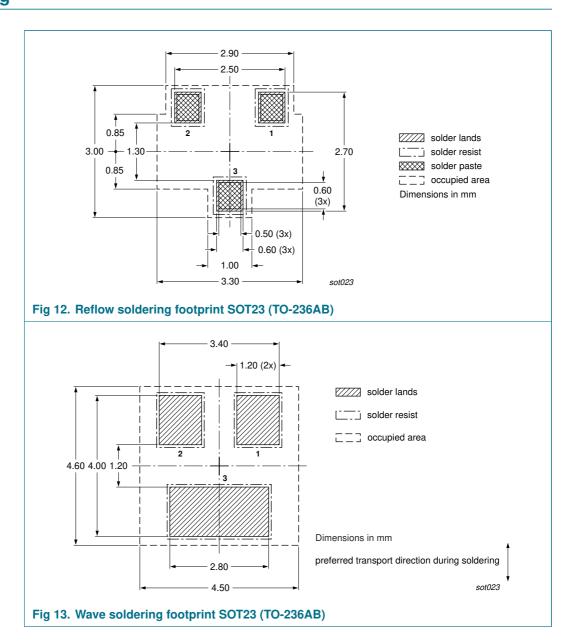
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	age Description		Packing quantity	
				3000	10000
PBRP113ZT	SOT23	4 mm pitch, 8 mm tape and reel		-215	-235

^[1] For further information and the availability of packing methods, see Section 13.

10. Soldering



PNP 800 mA, 40 V BISS RET; R1 = 1 k Ω , R2 = 10 k Ω

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBRP113ZT_1	20080116	Product data sheet	-	-

PNP 800 mA, 40 V BISS RET; R1 = 1 k Ω , R2 = 10 k Ω

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [2] The term 'short data sheet' is explained in section "Definitions"
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NXP Semiconductors

PBRP113ZT

PNP 800 mA, 40 V BISS RET; R1 = 1 k Ω , R2 = 10 k Ω

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